

/ Descriptions

Silicon NPN transistor in a SOT-323 Plastic Package.

/ Features

Low C_{ob} , complements the 2SA1577.

/ Applications

Medium power transistor.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Base PIN 3 Collector

/ Marking

h_{FE} Classifications	P	Q	R
Symbol			
h_{FE} Range	82 180	120 270	180 390
Marking	HCP	HCQ	HCR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

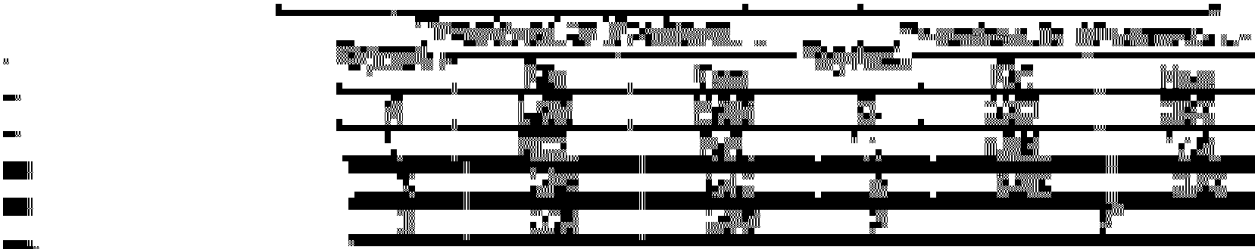
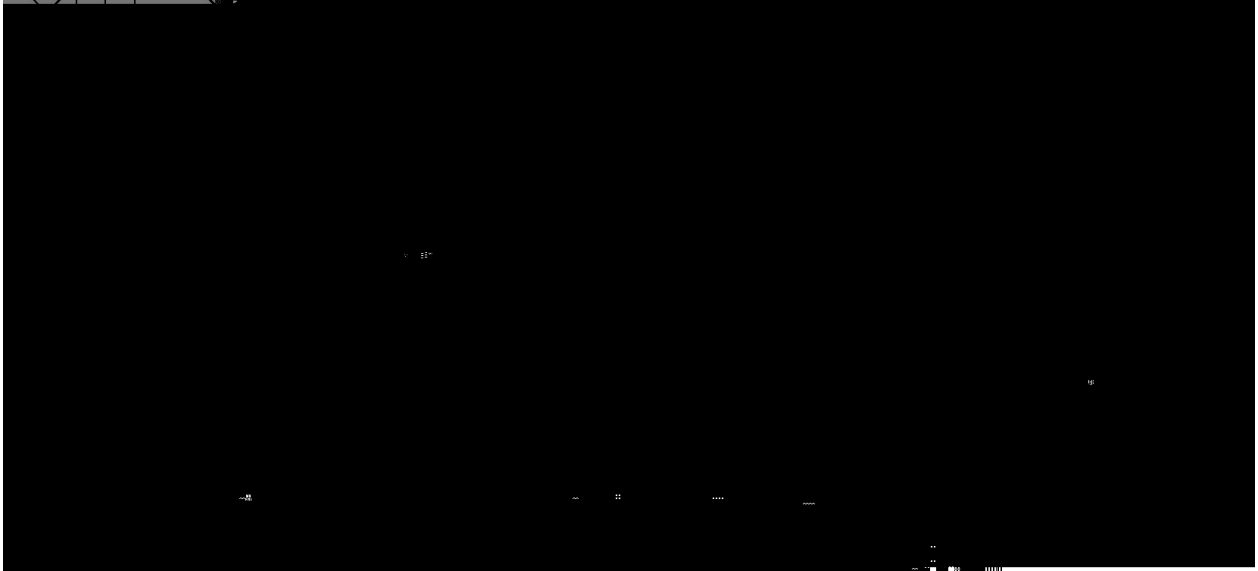
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\text{ A}$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0\text{mA}$ $I_B=0$	32			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=100\text{ A}$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=20\text{V}$ $I_E=0$			1.0	A
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=4.0\text{V}$ $I_C=0$			1.0	A
DC Current Gain	h_{FE}	$V_{CE}=3.0\text{V}$ I_C I				

/ Electrical Characteristic Curve

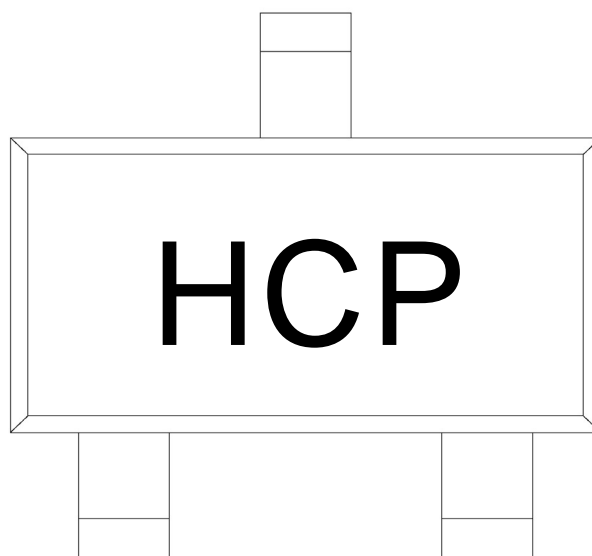
/ Package Dimensions

SOT-323

单位: mm



/ Marking Instructions



H

C

P

h_{FE}

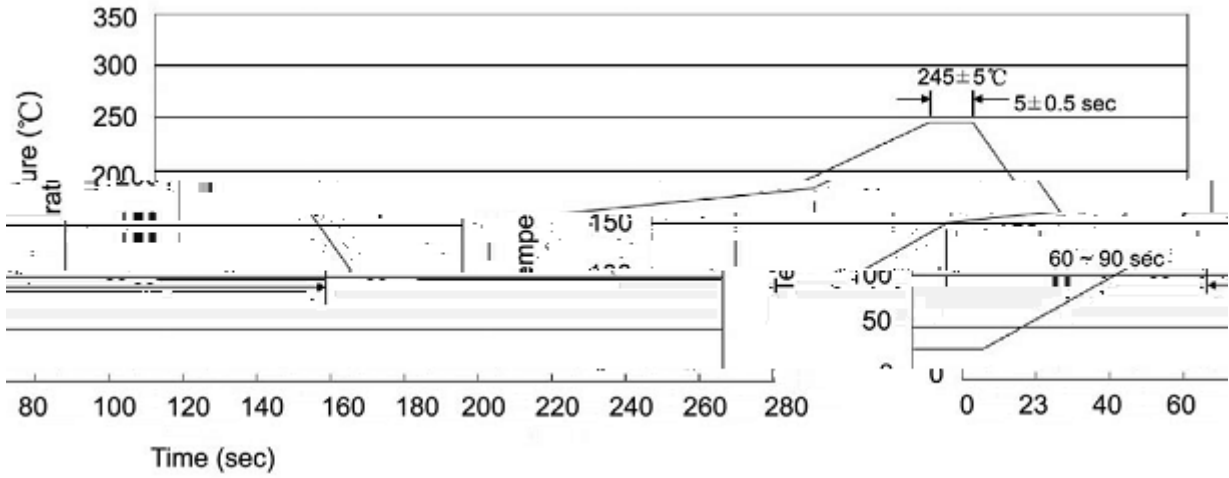
Note:

H: Company Code.

C: Product Type.

P: h_{FE} Classifications Symbol

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Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. |